

# Space Applications at NASA/GSFC Using Geant4

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#### Outline

- Introduction
- Angular Effects in Proton-Induced Single-Event Upsets
- Radiation Effects in Focal Plane Arrays
- Future Plans



#### Introduction

- Why do we think Geant4 is important to NASA?
  - Need one code with these features
    - Z > 4 particle interactions
    - Tracking of all secondaries
    - CAD interface
    - Easy to simulate sensitive volume for Single Event Effects (SEE)
- Current focus is SEE
  - Single Event Upsets (SEU) in logic devices
  - Single Event Transients (SET) in FPA
- Applications for TID and DD are under review



#### Angular Effects in Proton-Induced Single-Event Effects

Dominant mechanism for SEUs can be

 $1 < LET_c(MeV \bullet cm^2/mg) < 15$ 

- Elastic nuclear scattering
- Spallation reactions
- Some combination of both
- The incident proton energy will determine the dominant mechanism
- There is an angular dependence on the recoil direction
  - How does this affect an SOI/SOS device's SEU response?



#### **Motivation**

**Peregrine Prescaler** 

#### SOS technology

#### Honeywell SRAM

SOI technology









#### **Energy Dependence**

- Spallation reaction products dominate the SEU response for proton energies > 50 MeV
- For 63 MeV protons:

Dominant mechanism for reactions for LETs > 3 MeV•cm<sup>2</sup>?



#### Proton Interactions with Target Nucleus-Elastic Scattering



- Recoil pathlength decreases as angle increases
- On average, more charge is deposited when proton is normal to larger surface of SV
- Angular dependence cannot be explained by nuclear elastic scattering



## **Proton Interactions with Target Nucleus-Spallation Reactions**



- Recoil pathlength increases as angle increases
  - On average, more charge
    is deposited when proton is
    at some angle wrt to larger
    surface of SV
  - Spallation reaction is the mechanism



#### **63 MeV Inelastic Recoils in Si**





#### **200 MeV Inelastic Recoils in Si**





#### **Energy Dependence**



#### **Conclusions (#1) and Future Plans**

- Geant4 provided the physics simulation to uncover the basic mechanism for SEU in thin SOI/SOS technologies
- Plans to develop Geant4 SEE simulations
  - Incorporation of sensitive volume model
  - Incorporation of a charge collection model for proton induced events for complex transistor structures



- Goal is to predict Focal Plane Array (FPA) response to incident particles (protons, heavy ions, electrons) with high fidelity
  - Charge contamination on a pixel-by-pixel basis
- Source term is external radiation environment and transport through material surrounding FPA
  - L2 environment is predominantly galactic cosmic rays and solar particles



Note that secondaries and delta electrons are time coincident with primary and have limited range



#### Need Accurate Estimate of Transients

- Most primary and secondary particles can add to the noise floor (goal is 3-10 e<sup>-</sup>)
- Ionization energies for 5 μm HgCdTe and InSb detector material is on order of 1 eV/e-h pair
- Pathlengths are on order of 10  $\mu m$ 
  - Need only 3 to 10 e-h pairs/ $\mu$ m
  - Note that a 1 GeV proton in HgCdTe will create 1160 e-h pairs/µm





#### **Transport Calculations**

- Material Studies
  - Perform simulations for secondary environment

 $\begin{array}{c} \text{Material Region} \\ \text{Void Region} \\ \text{Void Region} \\ \text{CR Min Proton Spectrum} \\ \end{array}$ 

Contraction of the second s



#### **Secondary Environment**

#### Comparison of MCNPX and MuLaSSiS





#### **Activation Studies**

 Proton and neutron fluxes along with reaction cross-sections for spacecraft materials determine number of activated nuclei



#### **Transient Analysis**

- Supply location, trajectory, particle type, energy, and temporal information for every particle incident on FPA
- FPA model will use these inputs to calculate the transient rate for relevant environments, configurations and conditions

### Conclusions (#2) and Future Efforts

- We are currently focused on determining the frequency of occurrence, magnitude, and pulse width distributions of radiation induced transients in infrared FPAs used on JWST
- Purpose of transport studies is to provide reliable estimates of transported primary and secondary environment as input to:
  - Contamination and activation analysis
  - Transient analysis